October 25 – 27, 2007
Hilton Hotel, Dresden, Germany

www.icpt2007.com

in cooperation with:
German CMP User Group
Japanese Planarization and CMP Technical Committee (JSPE)
Korea CMP User Group (KCMPUG)
Northern California Chapter AVS (NCCAVS) CMPUG
Taiwan CMP User Group (CMPUGTW)
Conference Objective

Over the last 15 years, Chemical Mechanical Polishing (CMP) has developed into one of the key technologies in the ULSI fabrication process. It can be viewed as an enabling technology for manufacturing state-of-the-art microprocessors, high-density memories and other advanced microelectronic circuits. Without CMP, accurate printing of nanometer chip structures is impossible. CMP has helped to introduce multilevel interconnection and the employment of copper metallization. Emerging CMP applications include MEMS and nanotechnology, but advancements in CMP also stimulate related areas like wafer polishing and production of optical surfaces. In order to keep pace with future ULSI developments, improved Chemical Mechanical Polishing processes have to be available for FEOL and BEOL applications. For reasons of productivity enhancement, tool reliability improvements, cost reductions, process automation and advanced process control are required. Finally, new fields of applications for CMP, which certainly exist plentiful, have to be discovered and developed.

Upon several requests towards increased co-operation of the local CMP users groups from Germany, Japan, Korea, Taiwan, and the United States of America, the idea of a joint international CMP conference emerged in 2005. Following successful conferences in Tokyo, Japan (PacRim-CMP 2004), Seoul, Korea (PacRim-CMP 2005) and Foster City, California, USA (ICPT 2006), the International Conference on Planarization/CMP Technology ICPT 2007 in Dresden, Germany, is organized by the German CMP User Group within the German VDE/VDI-Society Microelectronics, Micro- and Precision Engineering. The mission of this conference is the provision of a forum for the worldwide CMP community for exchange and discussion on a high scientific level in order to support and advance the developments of this highly important field of semiconductor manufacturing.

Dr. Gerfried Zwicker
Fraunhofer Institute for Silicon Technology (ISIT)
Conference Chairman
Organizing Committee

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Organizer

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PROGRAM OVERVIEW

Wednesday, October 24, 2007

17:00 h  Registration
- 19:00 h

19:00 h  Set up for Technical exhibition

Thursday, October 25, 2007

07:30  Registration

09:00  Welcome to Conference
       G. Zwicker, Fraunhofer Institute for Silicon Technology, Itzehoe, Germany

09:05  Challenges and opportunities of semiconductor manufacturing between research and volume production
       H. Deppe, AMD Dresden, Germany

Session 1:  CMP Fundamentals 1
       Session Chairs:
       S.V. Babu, Clarkson University;
       Peter Thieme, Qimonda

09:30  CMP Modeling as a Part of Design for Manufacturing (Invited)
       S. Tripathi, A. Monvoisin, D. Dornfeld,
       F.M. Doyle;
       University of California at Berkeley, CA, USA

       S. Lawing, C. Juras;
       Rohm and Haas Electronic Materials, Phoenix, AZ, USA
10:15 Tribological, Kinetic, Thermal and Flow Characteristics of Retaining Rings in STI CMP
X. Wie1, A. Philipossian1,2, Y. Zhuang1,2, Y. Sampurno1, F. Sudargho1,2, C. Wargo3, L. Borucki2;
1University of Arizona, Tucson, AZ, USA;
2Araca Inc, Tucson, AZ, USA;
3Entegris Corp., Billerica, MA, USA

10:35 In-Situ Investigation of Wafer-Slurry-Pad Interactions during CMP
C. Gray1, A. Mueller1, J. Vlahakis1, V.P. Manno1, C. Rogers1, R. White1, S. Anjur2, M. Moinpour3,
1Tufts University, Medford, MA, USA;
2Cabot Microelectronics Corp., Aurora, IL, USA;
3Intel Corp., Santa Clara, CA, USA

10:55 Coffee Break

Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)

Session 2: Metal CMP 1
Session Chairs:
Yohei Yamada, Hitachi;
Karl Hensen, BASF

11:55 CMP of a Ru Based Layer in an Advanced Cu Low-k Stack (Invited)
J. Vaes1, F. Sinapi1, J. L. Hernandez1, G. Santoro2, O. Nguyen2, J. Wang3;
1IMEC, Heverlee, Belgium;
2Applied Materials, Heverlee, Belgium;
3Applied Materials, Sunnyvale, CA, USA

12:20 Integrated Profile Control from ECP to CMP
U. Stöckgen, S. Wehner, A. Preuße, J. Heinrich, J. Groschopf; AMD Fab36, Dresden, Germany

12:40 A Systematic Study on the Impact of Polymer Additives in Bulk Copper Slurry on Copper CMP
H. Chou, W.L. Kim, J.I. Noh, I. Lee;
Samsung Cheil Industries, Korea
13:00 Full Sequence eCMP for Advanced Low Stress Copper Planarization
1AMD Fab36, Dresden, Germany;
2Applied Materials, Dresden, Germany;
3Applied Materials, Sunnyvale, CA, USA

13:20 Lunch / Coffee
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)

Session 3: Wafers and New Materials
Session Chairs:
Haedo Jeong, Pusan National University;
Knut Gottfried, Fraunhofer IZM Chemnitz

14:50 Challenges in CMP of New Materials from Carbon Nanotubes to Moisture Sensitive Surfaces (Invited)
Y. Li, Clarkson University; Potsdam, NY, USA

15:15 Influence of the Wafer Shape on Polishing Performance for 300 mm Prime Wafer Polishing
M. Langenkamp, J. Kanzow, G. Mörsch; Peter Wolters AG, Rendsburg, Germany

15:35 Application of CMP to the Cladding Layer of MRAM
S.-H. Wang, D.-Y. Shu, K.-C. Lin, C.-T. Yen, M.-J. Tsai; Industrial Technology Research Institute, Hsinchu, Taiwan

15:55 TaN Formation by CMP for Cross-Spacered Phase Change Memory
K.-C. Lin, C.-W. Chen, S.-H. Wang, D.-Y. Shu, M.-J. Tsai, M.-J. Kao; Industrial Technology Research Institute, Hsinchu, Taiwan

16:15 Coffee Break
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)
Session 4: Poly-Si & Dielectric CMP 1

Session Chairs:
Mansour Moinpour, Intel;
Dorit Wecker, Infineon Technologies

17:15 Planarization of the Poly-Si Gate for Non-Volatile Memories (Invited)
L. Baud¹, L. Canevari², C. Romanelli², G. Spinolo², M. Rivoire³;
¹CEA-LETI, Grenoble, France;
²ST Microelectronics, Agrate Brianza, Italy;
³ST Microelectronics, Crolles, France

17:40 Effect of Polish Stopper Film in STI-CMP for 45nm Node Devices and Beyond
T. Watanabe¹, S. Shibata¹, N. Idani¹, M. Kase¹, M. Miyajima¹;
¹Fujitsu Ltd., Tokyo, Japan;
¹Fujitsu Laboratories Ltd., Tokyo, Japan

18:00 Influence of STI Trench Fill and Dummy Design on CMP Behavior
P. Ong¹, K. Devriendt¹, A. Redolfi¹, Y. Okuno², J.L. Hernandez¹;
¹IMEC, Leuven, Belgium;
²Matsushita, Japan

18:20 Defectivity Improvement for Fixed Abrasive Based STI CMP in Advanced Logic Technology
B. Reinhold¹, J. J. Gagliardi², S. Endle²;
¹AMD Fab36, Dresden, Germany;
²3M Electronics Markets Materials Division, St. Paul, MN, USA

18:40 End of Sessions (Day 1)

19:30 Conference Dinner
at the Pulvertum
An der Frauenkirche 12, 01067 Dresden
Thursday, October 25, 2007
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals

Insitu Studies of Copper CMP with Arginine and Peroxide Based Slurries
Y. Nagendra Prasad, S. Ramanathan; Indian Institute of Technology-Madras, Chennai, India

Bench Top Dual Mode eCMP Polisher with Multi Sensing Metrology
N. Gitis, V. Khosla, M. Vinogradov; CETR, Campbell, CA, USA

Charakterization of Residual Stress Change of Dielectrics in W-CMP Process Using Finite Element Method Analysis
A. Fukuda¹, Y. Mochizuki¹, H. Hiyama¹, M. Tsujimura², ¹Ebara Research Co., Ltd., Kanagawa, Japan; ²Ebara Corp., Kanagawa, Japan

The Study of CVD Diamond Conditioner
N. Rikita, R. Matsuki, H. Kobayashi, M. Nakamura, K. Chida; Mitsubishi Materials Corp., Saitama, Japan

Voltage-Activated Electrochemical Reactions of Copper for Electrochemical Mechanical Polishing Applications
Y.-J. Seo¹, S.-I. Lee¹, S.-W. Park², S.-J Han², Y.-K. Lee², W.-S. Lee²; ¹Daebul University, South Korea; ²Chosun University, South Korea

Effect of Pad Hole on ECMP Process
S. Jeong¹, H. Lee¹, J. Park¹, H. Jeong¹, H. Kim¹; ¹Pusan National University, Busan, Korea; ²Korea Institute of Industrial Technology, Busan, Korea
Next Generation Barrier CMP Technology for 45nm and Beyond
C. Ye, H. Li; Rohm and Haas Electronic Materials CMP Technology, Newark, DE, USA

Poly-CMP Integration for Sub 90 nm Self-aligned Floating Gate Flash Memories
M. Mariani, C. Romanelli, L. Canevari; ST Microelectronics, Agrate Brianza, Italy

Pre-polishing Transient Effects Investigation for Chemical Mechanical Planarization Processes
A. Filippini¹, C. Patini²;
¹ST Microelectronics, Agrate Brianza, Italy;
²Applied Materials, Caponago, Italy

Effect of Ceria Size and Concentration in Shallow Trench Isolation (STI) Chemical Mechanical Polishing (CMP)
S. Pandija¹, G. Crinière², C. Ceintrey², S.V. Babu¹;
¹Clarkson University, Potsdam, NY, USA;
²Rhodia Electronics and Catalysis, France

Next Generation Chemical Mechanical Planarization Slurries for Polishing Silicon on Advanced Devices
M. L. White, C. W. Nam, F. Batllo, A. Walters; Cabot Microelectronics Corp., Aurora, IL, USA

Control of Flatness for Chemical Mechanical Planarization
A. Nutsch, L. Pfitzner; Fraunhofer Institute for Integrated Systems and Device Technology, Erlangen, Germany

A Study on Delamination of Low-k Dielectrics During Cu-low k CMP
J.-H. Han¹, D.-H. Chung¹, B.-R. Park¹, J.-B. Yim¹,
T.-H. Ahn¹, J.-G. Park²;
¹Samsung Electronics Ltd., Kyunggi-Do, Korea;
²Hanyang University, Ansan, Korea

Effect of Slurry pH on Poly Silicon CMP
Y.-J. Kang¹, B.-K. Kang¹, J.-G. Park², Y.-K. Hong²,
S.-Y. Han², S.-K. Yun², B.-U. Yoon², C.-K. Hong²,
¹Hanyang University, Ansan, Korea;
²Samsung Electronics, Hwasung, Korea
Development of Post Ru CMP Cleaning Solutions
I.-K. Kim, B.-G. Cho, T.-G. Kim, J.-G. Park; Hanyang University, Ansan, Korea

Pad Roughness Effects on Removal Rate and Selectivity in a STI Ceria CMP Process
F. C. Meyer¹, C.-H. Kuo², C. Rudolph¹, P. Faustmann¹; ¹Qimonda, Dresden, Germany; ²Nanya Technology Corp., Taoyuan, Taiwan

CMP Issues Arising from Novel Materials and Concepts in the BEOL of Advanced Microelectronic Devices
K. Gottfried¹, I. Schubert¹, K. Schulze², S. Schulz², T. Gessner¹,²; ¹Fraunhofer-Institute Reliability and Micro-Integration, Chemnitz, Germany; ²Technical University Chemnitz, Germany

Impact of Ceria Properties and CMP Parameters on STI CMP Performance
J. De Messemaeker¹, F. Sinapi², P. Ong², S. Put³, D. Nelis¹, J. van den Bosch¹, Y. Strauven¹, P. Lippens¹, K. Devriendt²; ¹Umicore R&D, Olen, Belgium; ²IMEC, Leuven, Belgium

Major Influences of Shaping and Profiling of Cu ECP and CMP on Feature Level for Process Stabilizing
G. Marxsen, M. Nopper, T. Ortleb, M. Lehr, T. Merbeth, T. Roessler; AMD, Dresden, Germany

Advanced W-CMP Slurry for High Planarity
R. Tanaka, H. Nojo, K. Yoshida, A. Isobe; Nitta Haas Inc., Kyoto, Japan

New Polish Chemistry and Process for Improved Fixed Abrasive CMP Performance
G. Menk, R. Marks, G. Leung, A. Iyer, J. Diao, Y. Zhou, C. Lee; Applied Materials, Sunnyvale, Ca, USA

Improvement of Uniformity Post Oxide CMP by Optimization of Pre Processes
T. Schest, J. Plagmann, S. Willkofer; Infineon Technologies, Regensburg, Germany
Novel Chemicals and Mechanisms that Control Dishing and Overpolish Window Independent of Corrosion Inhibitor Effects
S. Shrauti, B. Palmer, A. Meyers, G. Zhang, A. Zutshi; DuPont Air Products NanoMaterials, Tempe, AZ, USA

Application of the Copper Damascene Process for the Preparation of Electromigration Test Structures
M. Stangl¹, V. Hoffmann¹, K. Wetzig¹, U. Künzelmann², J.-W. Bartha²;
¹Leibniz-Institute for Solid State and Materials Research (IFW) Dresden;
²Dresden University of Technology, Dresden, Germany
Friday, October 26, 2007

08:30  Morning Welcome
       G. Zwicker, Fraunhofer Institute for Silicon Technology, Itzehoe, Germany

Session 5:  Poly-Si & Dielectric CMP 2
            Session Chairs:
            Jin-Goo Park, Hanyang University; Georg Moersch, Peter Wolters AG

08:35  Materials & Metrology Challenges in Planarization and Interconnect Technologies (Invited)
       M. Moinpour; Intel, Santa Clara, CA, USA

09:00  Integrative Defect Reduction at STI CMP (Invited)
       R. Becker, W. Tittes, A. Boenicke, S. Peters, M. Probst, D. Schulze, S. Cwikla, S. Loesch; Infineon Technologies, Dresden, Germany

09:25  Novel Slurries for Achieving a Low Silicon Dioxide and High Silicon Nitride Removal During Chemical-Mechanical Planarization
       A. Natarajan, Dandu Veera P.R., S.V. Babu; Clarkson University, Potsdam, NY, USA

09:45  Applications of Shear Force Spectral Analysis in STI CMP
       Y. Sampurno¹, F. Sudargho¹², Y. Zhuang¹², T. Ashizawa¹, H. Morishima³, A. Philipossian¹²;¹
       University of Arizona, Tucson, AZ, USA;
       ²Araca Inc., Tucson, AZ, USA;
       ³Hitachi Chemical Co., Tokyo, Japan

10:05 Study of STI CMP Process Control on High Aspect Ratio Gap-fill Topographies by Motor Current EPD
       C.-H. Kuo¹, F. C. Meyer², M. Hollatz², P. Faustmann², K.-W. Chung¹, C.-K. Lin¹;¹
       ¹Nanya Technology Corp., Taoyuan, Taiwan;
       ²Qimonda, Dresden, Germany
10:25 Coffee Break
Poster Session 2: Defects and Metrology, New Materials, Slurry, Pad Conditioning
(all Posters in Poster Session 2 are listed on page 18)

Session 6: Metal CMP 2
Session Chairs:
Halbert Tam, JSR Micro;
Uwe Stöckgen, AMD

11:25 Copper Oxidization Formation Analysis for Improving TDBD Reliability (Invited)
Y. Yamada¹, Y. Yagi², N. Konishi¹, N. Ogiso²,
K. Katsuyama¹, S. Asaka¹, J. Noguchi¹,
T. Miyazaki²;
¹Hitachi Ltd., Tokyo, Japan;
²Sanyo Chemical Industries Ltd., Kyoto, Japan

11:50 Influence of Low-k Films on Barrier Removal Rate Variation Between Blanket and Patterned Wafers
Y. Li¹, C. Burkhard¹, C. Wang¹, R. Wen²,
D. Mahulikaar³;
¹Clarkson University, Potsdam, NY, USA;
²Planar Solutions, Mesa, AZ, USA

12:10 Evaluation of Cu CMP Barrier Slurries for Ultra Low-k Dielectric Film (k~2.4) for 45nm Technology
F. Zhao¹, L. Economicos³, W.-T. Tseng⁴,
H.-K. Kim¹, Edward Engbrecht⁵, Jing Hui Li¹,
Wu Ping Liu¹, M. Chae⁵, L. M. Nicholson⁶;
¹Chartered Semiconductor Manufacturing Ltd.;
²IBM Systems and Technology Group;
³Samsung Electronics Co., Ltd.;
⁴Infineon Technologies AG

12:30 Evaluation and De-coupling of Electrochemical and Mechanical Effects of Diluted WCMP Commercial Slurry on Tungsten Removal Rate
D. M. Gianni¹,², A. Mazzarolo¹, N. Masciocchi²,
A. Maspero⁶, G. Spinolo⁶, A. Vicenzo³;
¹STMicroelectronics, Agrate Brianza, Italy;
²Università dell' Insubria, Como, Italy;
³Politecnico di Milano, Milan, Italy
12:50  Lunch / Coffee
Poster Session 2: Defects and Metrology, New Materials, Slurry, Pad Conditioning
(all Posters in Poster Session 2 are listed on page 18)

Session 7:  Defects and Metrology
Session Chairs:
Keiichi Kimura, Kyushu Institute of Technology;
Johann Wolfgang Bartha, Dresden Technical University

14:20  Post-CMP Cleaning: Interaction between Particles and Surfaces (Invited)
J.-G. Park; Hanyang University, Ansan, Korea

14:45  Wafer Edge / Bevel Treatment of Device Wafers by Means of CMP
A. Wieters, P. Thieme; Qimonda, Dresden, Germany

15:05  Impacts on Microscratching in CMP Processes in High Volume Production
G. Marxsen, S. Lingel, J. Schlott, A. Hoefgen; AMD, Dresden, Germany

15:25  Oxide Thickness Profile Measurement by Dispersive White-Light Interferometry (Invited)
H. Jeong¹, B. Park², Y. Kim¹, H. Kim², Y. Ghim³, J. You¹, S. Kim³;
¹Pusan National University, Busan, Korea;
²Korea Institute of Industrial Technology, Busan, Korea;
³Korea Advanced Institute of Science and Technology, Daejon, Korea

15:50  Coffee Break
Poster Session 2: Defects and Metrology, New Materials, Slurry, Pad Conditioning
(all Posters in Poster Session 2 are listed on page 18)
Session 8: CMP Fundamentals 2
Session Chairs:
Ara Philipossian, University of Arizona;
Katrin Blum, IHP Frankfurt/Oder

16:45 Full-Chip CMP Simulation System (Invited)
D. Fukuda¹, T. Shibuya¹, N. Idani²,
T. Karasawa³;
¹Fujitsu Laboratories Ltd., Kawasaki, Japan;
²Fujitsu Ltd, Kawasaki, Japan

17:10 Greenwood-Williamsson Model for Pattern-Dependent Planarization
R. Rzehak, B. Vasilev; Qimonda, Dresden, Germany

17:30 Study on Material Removal Phenomena in CMP Process
K. Kimura¹, Y. Hashiyama¹,
P. Khajornrungruang¹, H. Hiyama²,
Y. Mochizuki³;
¹Kyushu Institute of Technology, Fukuoka, Japan;
²Ebara Research, Kanagawa, Japan

17:50 Modeling and Optimal Control of Chemical Mechanical Planarization
S. Dürigen¹,², P. Benner¹, U. Stöckgen²,
J. Heinrich³;
¹Technical University Chemnitz, Germany;
²AMD Fab36, Dresden, Germany

18:10 End of Sessions (Day 2)
Friday, October 26, 2007
Poster Session 2
Defects and Metrology, New Materials, Slurry, Pad Conditioning

Development of Planarity Improved Abrasive-Free Copper CMP Slurry and Practical Non-Selective Barrier CMP Slurry Based on Electrochemical Study
J. Amanokura¹, K. Mabuchi², T. Sakurada¹, Y. Nomura¹, M. Habiro¹, H. Akahoshi²;
¹Hitachi Chemical Co., Ltd., Hitachi, Japan;
²Hitachi Ltd., Hitachi, Japan

The Organic Diamond Disk (ODD) for Dressing Polishing Pads of Chemical Mechanical Planarization
J. C. Sung¹, C.-S. Chou¹, M. Sung²;
¹KINIK Company, Taipei, Taiwan;
²Advanced Diamond Solutions, San Francisco, CA, USA

Modeling for Pad Wear Control During Conditioning in CMP
T. Kasai, S. Anjur, H. Siriwardane, P. Feeney; Cabot Microelectronics Corp., Aurora, IL, USA

The Fabrication of Ideal Diamond Disk (IDD) by Casting Diamond Film on Silicon wafer
J. C. Sung¹, Y.-T. Chen², M.-C. Kan¹, H.-K. Chang¹, M. Sung²;
¹KINIK Company, Taipei, Taiwan;
²National Defense University, Taoyuan, Taiwan;
³Advanced Diamond Solutions Inc., San Francisco, CA, USA

Three-Dimensional Metrology for CMP Process Evaluation with In-line Wide-Area Atomic Force Microscope
K. Murayama, T. Morimoro, Y. Kunitomo, M. Edamura, S. Sekino, T. Kurenuma; Hitachi-kenki Fine Tech Co., Ltd., Ibaraki, Japan

Pad Surface Microstructure and Optimization of the Conditioning Sweep
L. Borucki¹, X. Wei², Y. Zhuang¹,², A. Philipossian¹,², D. Slutz³;
¹Araca Inc., Tuscon, AZ, USA;
²University of Arizona, Tucson, AZ, USA;
³Morgan Advanced Ceramics, Allentown, PA, USA
Improvements of Electrical and Optical Property of Organic Light Emitting Diode Using Chemical Mechanical Polishing Process
G.-W. Choi¹, W.-S. Lee¹, Y.-J. Seo²;
¹Chosun University, South Korea;
²Daebul University, South Korea

Development of AE Monitoring System for CMP Process
S. Park¹, S. Joo¹, Y. Kim¹, H. Jeong¹, H. Kim²;
¹Pusan National University, Busan, Korea;
²Korea Institute of Industrial Technology, Busan, Korea

Reduction of Dishing in Polysilicon CMP for MEMS Application by Using Protective Layer and High Selectivity
W. Shin¹, S. Park², H. Kim³, K. Park¹, H. Cho¹, S. Joo¹, H. Jeong¹;
¹Pusan National University, Busan, Korea;
²University of California, Berkeley, CA, USA;
³Korea Institute of Industrial Technology, Busan, Korea

Experimental Analysis on CMP Mechanism of Single Crystal SiC
H. Lee¹, S. Jeong¹, H. Seo¹, B. Park¹, J. Oh¹, H. Jeong¹, H. Kim²;
¹Pusan National University, Busan, Korea;
²Korea Institute of Industrial Technology, Busan, Korea

Optimized and Customized CMP Conditioner Design for Next Generation Oxide/Metal CMP
T. Hwang, R. Vedantham, T. Putthanangady; Saint-Gobain High Performance Materials, Northboro, MA, USA

Impact in the Conditioning and Cleaning of Unwoven Fabric Polyester Pads with a High Pressure Micro Jet (HPMJ) on Silicon Polishing
K. Miyachi¹, Y. Seike², S. Haba², S. Kurokawa³, T. K. Doi³;
¹Asahi Sunac Corp., Aichi, Japan;
²Nitta Haas Inc., Tokyo, Japan;
³Kyushu University, Fukuoka, Japan

Large Particle Counting for Quality Control of CMP Slurries
A. Nogowski¹, M. Stintz¹, H. Barthel²;
¹Technical University Dresden, Germany;
²Wacker-Chemie AG, Burghausen, Germany
Prime Wafer Geometry Improvement During Haze-free Polishing with Peter Wolters Polishing Head “M-Carrier”
J. Kanzow, M. Langenkamp, G. Mörsch; Peter Wolters AG, Rendsburg, Germany

Damascene Metal Gate Technology: A Front-end CMP Based Universal Platform for High-k Evaluation at the Device Level
R. Endres, U. Schwalke; Technical University Darmstadt, Germany

Defectivity Reduction in a Poly-Si CMP for SAFG Definition (in NOR Application)
L. Canevari, C. Romanelli, G. Spinolo, V. Bontempo; ST Microelectronics, Agrate Brianza, Italy

Development of Copper Post-CMP Cleaning Chemistries Compatible with Advanced Barrier Materials
D. Tamboli, M. Rao, G. Banerjee; Air Products and Chemicals, Allentown, PA, USA

Post-CMP Clean PVA Brush Design Advancements and Characterization in Cu/Low-k Applications
R. K. Singh, C. R. Wargo, D. W. Stockbower; Entegris Inc., Billerica, MA, USA

Laser Scattering Technique for Characterizing Defects and Surface Morphology in the Fixed Abrasive CMP Process
J. Gagliardi¹, E. Olson¹, U. Mahajan², H. Zhang², C. Douglas²;
¹3M Corporation, St. Paul, MN, USA;
²KLA-Tencor Corporation, Milpitas, CA, USA

Enhanced Control and Manufacturing for CMP Processing with Advanced Blending and Delivery of Slurries
G. Liu, R. Moulton, L. Han, G. Flores; ChemFlow Systems Inc., San Jose, CA, USA

Conditioning of CMP Pad to Reinstate Pad Surface Function
K. Kadomura¹, T. Fukunishi², Y. Umezaki³, S. Kurokawa³, T. Doi³;
¹A.L.M.T. Diamaond Corp.; Hyogo, Japan;
²A.L.M.T. Corp., Hyogo, Japan;
³Kyushu University, Fukuoka, Japan
Effect of Diamonds on Pad Recovery in Oxide and Metal Pad Conditioning Process
B.-K. Kang¹, Y.-J. Kang¹, K.C. Kim¹, J.-G. Park¹
J.-H. Lee², J.-S. Ahn³;
¹Hanyang University, Ansan, Korea;
²Ehwa Diamond Ind. Co., Ltd., Osan, Korea

Accelerating Development Timeframes Through Effective Use of CMP Outsourcing
R. Carroll¹, L. Rhoades²;
¹Polar Semiconductor Inc., USA;
²Entrepix Inc., Tempe, AZ, USA

Point of Use Quality Control of CMP Slurries
F. Hinze, J. Altmann; Aello, Dresden, Germany

Optimizations of Post Polish Procedure for Defect Density Reduction
H. Lauber, S. Muenzberger; Infineon Technologies, Dresden, Germany

Fabrication of Surface Acoustic Wave Structures with buried Copper IDTs using the Copper Damascene Process
S. Menzel¹, D. Reitz¹, U. Künzelmann², M. Albert²,
J.-W. Bartha³;
¹Leibniz-Institute for Solid State and Materials Research (IFW), Dresden;
²Dresden University of Technology, Dresden, Germany

Material & Design Considerations for Zero Defect CMP Pads
R. Carpio¹, F. Tolic¹, S. Hymes², R. Bajaj³;
¹ATDF, Austin, TX, USA;
²SemiQuest Inc., San Jose, CA, USA
Saturday, October 27, 2007

Social Day
“World Heritage Discovery Tour”

Experience the Dresden Elbe valley from the land, from the air and from the water. During a combined walking and coach tour, we would like to introduce a cultural landscape which has evolved over the course of 800 years. Learn more about the famous sights of the city, such as the Zwinger, Semper Opera House and Frauenkirche. The journey continues past broad green meadows and below the so-called Elbe palaces to the oldest suspension railway in the world.

From the Loschwitz Heights, you can enjoy a magnificent view over the whole Elbe valley. The next stopping point is no less fascinating: Pillnitz Palace and Park. During a tour of the complex, you will become acquainted with the history, architecture and landscape gardening of this unique integral work of art. Alongside the dendrological treasures of the park, we will also show you around one of its pavilions, the Catholic palace chapel and the historical palace kitchens. During the return journey to Dresden aboard a paddle-steamer, you can relax and absorb once more the harmony of urban and natural landscapes.

09:00 h     Tourist Guide starts the walking tour at the Theaterplatz/Reiterdenkmal near the Semper Opera House
16:45 h     End of tour at the Elbeterassen

Please make your registration in good time. Bookings for excursions will be made on a “first come - first served” basis upon receipt of registration and payment.

The total amount shall be paid in advance or at the registration desk and has to be made in EUR.
CONFERENCE INFORMATION

CONFERENCE HOURS
Thursday, October 25, 2007 09:00 h to 18:40 h
Friday, October 26, 2007 08:30 h to 18:10 h

REGISTRATION HOURS
Wednesday, October 24, 2007 17:00 h to 19:00 h
Thursday, October 25, 2007 07.30 h to 09:30 h

EXHIBITION
The two-day tabletop exhibition is an integral part of the ICPT 2007 conference and takes place at an exhibition area close to the conference lecture room which can be visited during all coffee and lunch breaks.

Exhibition space of 4 m² or 6 m² (40 sqft or 60 sqft) with table, two chairs and poster board are available. Registration for the exhibition includes two full access badges, two copies of the proceedings and a company name listing in all promotional materials.

For further information on the exhibition please contact
Dr. Ronald Schnabel
Stresemannallee 15
D-60596 Frankfurt am Main, Germany
Phone: ++49-69-6308-330, Fax:++49-69-6308-9828
E-Mail: gmm@vde.com

INFORMATION FOR AUTHORS

MANUSCRIPTS AND PROCEEDINGS
Manuscripts should be send to conference-papers@vde.com by August 24, 2007. Since the manuscripts will be directly reproduced in the proceedings please send a pdf-file by e-mail. The manuscripts are limited to 6 pages (figures included). When writing respectively shaping your manuscript, please observe the "Instructions for paper preparation", which you will find at http://www.ICPT2007.com
The conference proceedings and CD-ROM will be published by the VDE/VDI Society Microelectronics, Micro- and Precision Engineering and will be delivered to the conference participants at the registration desk.

Please note that late submissions may not be considered in the conference proceedings.

GENERAL INFORMATION

ICPT 2007 SECRETARIAT
For detailed Information please contact:
VDE/VDI-Society Microelectronics, Micro- and Precision Engineering (GMM)
Dr. Ronald Schnabel
Stresemannallee 15
D-60596 Frankfurt am Main, Germany
Phone: ++49 69 / 6308-330
Fax: ++49 69 / 6308-9828
E-Mail: gmm@vde.com
During the conference:
Phone: ++49 171 4695 118

CONFERENCE FEES

<table>
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<th>until Sept. 25,2007</th>
<th>after Sept. 25,2007</th>
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<tr>
<td>Non-Members</td>
<td>€ 390,00</td>
<td>€ 440,00</td>
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<tr>
<td>VDE, VDI-Members*</td>
<td>€ 350,00</td>
<td>€ 400,00</td>
</tr>
<tr>
<td>Lecturer</td>
<td>€ 350,00</td>
<td>€ 400,00</td>
</tr>
<tr>
<td>Exhibitor (max. 2 people)</td>
<td>€ 0,00</td>
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<td>Non-Member-Students**</td>
<td>€ 40,00</td>
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<td>Student Members**</td>
<td>€ 20,00</td>
<td>€ 50,00</td>
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<tr>
<td>Extra proceedings</td>
<td>€ 60,00</td>
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<tr>
<td>Discovery tour 27.10.2007</td>
<td>€ 70,00</td>
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* Participants applying for the membership fee must include a copy of their membership card to the registration form.
** A photocopy of the student card must be included.

The conference fee includes admission to all sessions as well as to the daily coffee-breaks and lunches, one copy of the proceedings including a CD-ROM, conference dinner on Thursday.
CONFERENCE REGISTRATION

To register for ICPT 2007 please fill in the registration form attached to this program and return to VDE Conference Services, Stresemannallee 15, 60596 Frankfurt, Germany. To enjoy the “early-bird-discount”, VDE Conference Services must receive the form before September 25th, 2007. Full payment or credit card information must accompany all registrations in order to be accepted. Completed forms may be sent by fax (+49 69 96 31 5213) surface mail or e-mail (vde-conferences@vde.com). A confirmation of the registration will be sent upon receipt of full payment.

ONLINE REGISTRATION

Registrations for the conference may be done online on the conference homepage www.icpt2007.com

PAYMENT TO THE VDE/VDI SOCIETY

Payment for registration, including bank charges and processing fees, must be made in Euro.

The conference fee has to be fully paid in advance. Confirmation of registration will be sent after full payment has been received at the VDE-Conference Services.

The following methods of payment are accepted:

- Cheque in EURO (€) payable to VDE and sent together with the registration form by mail.

- By credit card authorisation as per registration form. The 16 digit card number, expiry date, security No. (last 3 digits on rear side of credit card) and holder’s name must be indicated on the registration form. Signature of the card holder is mandatory.

- Cash payment on-site in EURO (€)

CANCELLATION

In case of cancellation, provided that written notice is received at the VDE-Conference Services before Sept. 25, 2007, the registration fee will be fully refunded less a handling fee of EURO 60,00. After Sept. 25, 2007 no refund will be made. Proceedings and CD-ROM will then be sent to the registrant after the conference.
PROCEEDINGS

All papers accepted for presentation at the conference will be published with the proceedings and a CD-ROM. The proceedings will be handed on-site to all delegates attending the event.

Additional proceedings and CD-ROM are on sale during the conference (upon availability) at EURO 60.00

CONFERENCE VENUE

Hilton Dresden
An der Frauenkirche 5
D-01069 Dresden, Germany
Phone: +49 351/86420
Fax: +49 351/8642-725

Hilton Dresden, located in the heart of the old town, next to the Frauenkirche, is situated on Bruehl's Terrace. The Semper Opera House and the world-renowned "Zwinger" are within walking distance. The piers of the world's largest and oldest paddle steamer fleet are next to the hotel.

HOTEL RESERVATION

A block of rooms has been reserved for ICPT 2007 participants

Hilton Hotel Dresden
The hotel room rate (special rate, including breakfast) is

- 165.00 EURO (single room classic),
- 190.00 EURO (double room classic)
- 190.00 EURO (single room deluxe),
- 215.00 EURO (double room deluxe)
- 220.00 EURO (single room executive),
- 245.00 EURO (double room executive)

per night. Accommodation is not included in the conference fee. Please contact the Hilton Hotel, for reservation.

Hilton Dresden
An der Frauenkirche 5
D-01069 Dresden, Germany
Phone: +49 351 / 8642-0
Fax: +49 351 / 8642-725
E-Mail: info.dresden@hilton.com
http://www.hilton.com/
You should reserve your room by September 12th, 2007 or our block of rooms at the Hilton Hotel may be released by the hotel for general sale. Please use the following code for booking: “ICPT 2007”

**Ramada Hotel Dresden**

The hotel room rate (special rate, including breakfast) is

- 93,00 EURO (single room comfort),
- 107,00 EURO (double room comfort)

per night. Accommodation is not included in the conference fee. Please contact the Ramada Hotel for reservation.

Ramada Hotel Dresden  
Wilhelm-Franke-Straße 90  
D-01219 Dresden, Germany  
Phone: +49 351 / 4782-0  
Fax: +49 351 / 4782-550  
http://www.ramada-dresden.de

You should reserve your room by August 24th, 2007 or our block of rooms at the Ramada Hotel may be released by the hotel for general sale. Please use the following code for booking: “ICPT 2007”

All payments related to accommodation have to be made directly on departure in the hotel.

**BUSSHUTTLE**

There will be a bus shuttle from the Ramada Hotel to the Hilton Hotel on both conference days. The bus will depart half an hour before the beginning of the conference on Oktober 25 and 26, 2007.

**INSURANCE**

The organisers may not be held responsible for any injury to participants or damage, theft and loss of personal belongings.
PASSPORT AND VISA REQUIREMENTS

Foreign visitors entering Germany have to present a valid Identity Card or Passport. Delegates who need a visa should contact the German consular offices or embassies in their home countries. Please note that neither the VDE-Conference Services nor the VDE/VDI-Society Microelectronics, Micro- and Precision Engineering (GMM) or the supporting bodies are able to extend any "Invitation" for application of visa.

TRANSPORT

By Air
Dresden Airport
Distance from hotel: 10 km, Drive time: 20 min.
Directions: Follow signs to city centre. After passing the Elbe Bridge, turn right onto Terrassenufer. Follow Hilton signs.

Getting to and from the airport
Bus Service, typical minimum charge is EURO 8,00
Limousine, typical minimum charge is EURO 70,00
Taxi, typical minimum is EURO 25,00

By train
from Frankfurt in 5 hours
from Berlin in 3 hours
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<tr>
<th>LIST OF EXHIBITORS</th>
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<tr>
<td>3M Company, St. Paul, USA</td>
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<td>Abrasive Technology, Ohio, USA</td>
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<td>AGC Electronic Materials, Hillsboro, USA</td>
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<td>Araca, Inc., Tucson, US</td>
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<td>ATDF, Inc., Austin, USA</td>
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<td>ECO Physics AG, Dürnten, Suisse</td>
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<td>Ehwa Diamond Ind. Co. Ltd., Osan, Korea</td>
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<td>Entegris GmbH, Dresden, Germany</td>
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<td>Euris GmbH, Tübingen, Germany</td>
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<td>G&amp;P Technology, Inc., Busan, Korea</td>
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<td>JSR Micro N.V., Leuven, Belgium</td>
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<td>Kemesys, Peynier, France</td>
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<td>Mitsubishi Materials Corp., Tokyo, Japan</td>
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<td>Morgan Advanced Ceramics, Allentown, PA, USA</td>
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<td>Pall GmbH, Bad Kreuznach, Germany</td>
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<td>Qimonda AG, Dresden, Germany</td>
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<td>Rohm und Haas Electronic Materials, Dresden, Germany</td>
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<td>Samsung Cheil Industries Inc., Uiwang-Si, Geyoinggi-Do, Korea</td>
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<td>Shinan Diamond Industrial Co., Ltd., Incheon, Korea</td>
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<td>SPS-Europe B.V., Putten, The Netherlands</td>
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<td>Struers GmbH/Logitech Ltd, Willich, Germany</td>
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<td>Umicore, Olen, Belgium</td>
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The IPCT 2007 Organizing Committee would like to express its sincere appreciation to the following companies for their support:

Cabot Microelectronics
EHWA
Intel
JSR Micro
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Qimonda
Roan Technologies
Samsung
Cheil Industries
SPS
MiPox
Thomas West, Inc.